

N-Channel Enhancement Mode Power MOSFET

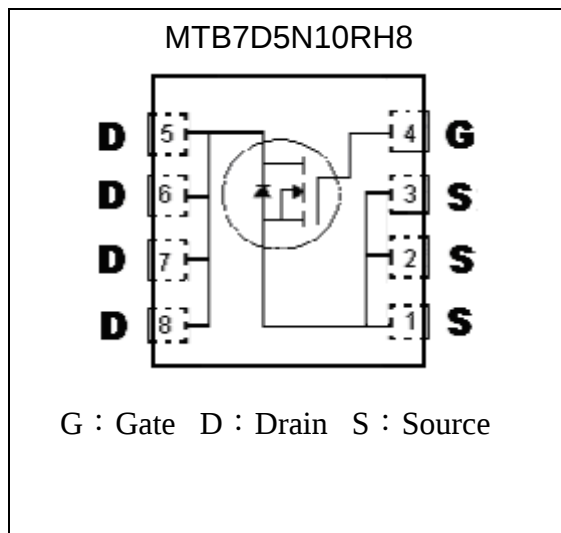
MTB7D5N10RH8

Features

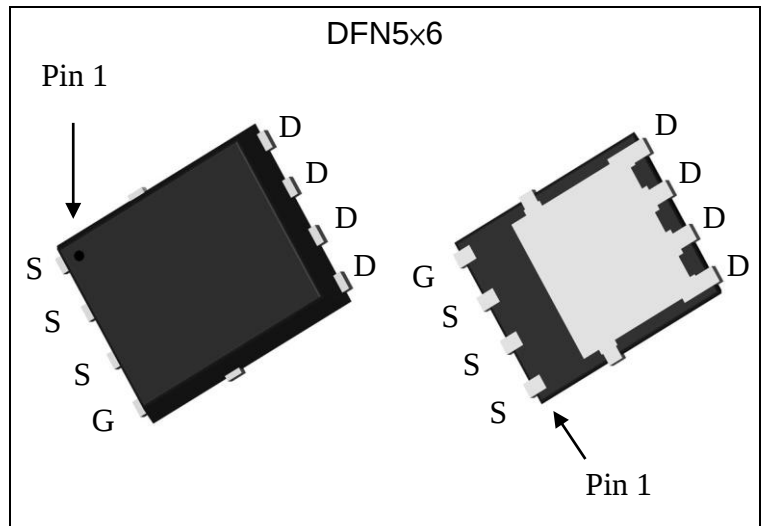
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

BV_{DSS}	110V
I_D@V_{GS}=10V, T_C=25°C	53A
I_D@V_{GS}=10V, T_A=25°C	11.8A
R_{DS(ON)}@V_{GS}=10V, I_D=20A	6.4mΩ (typ)
R_{DS(ON)}@V_{GS}=4.5V, I_D=16A	9.3 mΩ (typ)

Symbol

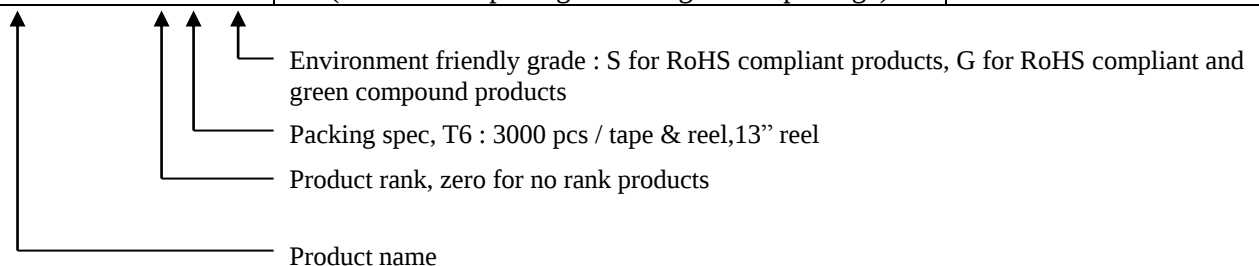


Outline



Ordering Information

Device	Package	Shipping
MTB7D5N10RH8-0-T6-G	DFN 5 ×6 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel



**Absolute Maximum Ratings** (Ta=25°C)

Parameter		Symbol	10s	Steady State	Unit
Drain-Source Voltage		V _{DS}	110		V
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current @ T _C =25°C, V _{GS} =10V (Note 1)		I _D	53		A
Continuous Drain Current @ T _C =100°C, V _{GS} =10V (Note 1)			33.5		
Continuous Drain Current @ T _A =25°C, V _{GS} =10V (Note 2)		I _{DSM}	17.8	11.8	
Continuous Drain Current @ T _A =70°C, V _{GS} =10V (Note 2)			14.2	9.4	
Continuous Drain Current @ T _A =85°C, V _{GS} =10V (Note 2)			12.8	8.5	
Pulsed Drain Current (Note 3)		I _{DM}	212 *1		
Avalanche Current @ L=0.1mH (Note 3)		I _{AS}	50		
Avalanche Energy @ L=1mH, I _D =20A, V _{DD} =25V (Note 4)		E _{AS}	200		mJ
Repetitive Avalanche Energy @ L=0.05mH (Note 3)		E _{AR}	5 *2		
Total Power Dissipation	T _C =25°C (Note 1)	P _D	50		W
	T _C =100°C (Note 1)		20		
	T _A =25°C (Note 2)	P _{DSM}	5.7	2.5	
	T _A =70°C (Note 2)		4.0	1.8	
	T _A =85°C (Note 2)		3.6	1.6	
Operating Junction and Storage Temperature Range		T _j , T _{stg}	-55~+150		°C

Thermal Data

Parameter		Symbol	Typical	Maximum	Unit
Thermal Resistance, Junction-to-ambient (Note 2)	t≤10s	R _{θJA}	18	22	°C/W
	Steady State		42	50	
Thermal Resistance, Junction-to-case		R _{θJC}	2	2.5	

Note : 1.The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2.The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

3.Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

4.100% tested by conditions of L=0.1mH, I_{AS}=20A, V_{GS}=10V, V_{DD}=25V

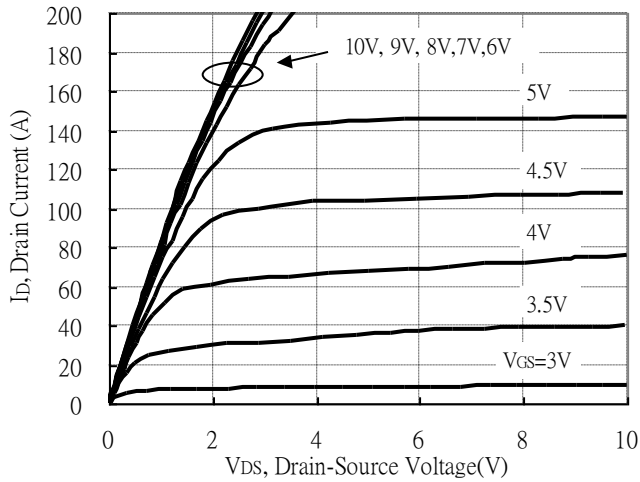
**Characteristics (Tj=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	110	-	-	V	V _{GS} =0V, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.08	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	1.5	-	2.5	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	40	-	S	V _{DS} =5V, I _D =20A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =90V, V _{GS} =0V
	-	-	25		V _{DS} =90V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	6.4	9	mΩ	V _{GS} =10V, I _D =20A
	-	9.3	14		V _{GS} =4.5V, I _D =16A
Dynamic					
*Q _g	-	53.9	-	nC	V _{DS} =80V, I _D =20A, V _{GS} =10V
*Q _{gs}	-	12.3	-		
*Q _{gd}	-	10	-		
*t _{d(ON)}	-	26.6	-	ns	V _{DS} =50V, I _D =13A, V _{GS} =10V, R _{GS} =6Ω
*t _r	-	8.2	-		
*t _{d(OFF)}	-	72.4	-		
*t _f	-	14.4	-		
C _{iss}	-	3480	-	pF	V _{GS} =0V, V _{DS} =50V, f=1MHz
C _{oss}	-	315	-		
C _{rss}	-	29	-		
R _g	-	0.9	-	Ω	f=1MHz
Source-Drain Diode					
*I _S	-	-	40	A	
*I _{SM}	-	-	160		
*V _{SD}	-	0.84	1.2	V	I _S =20A, V _{GS} =0V
*t _{rr}	-	45.2	-	ns	V _{GS} =0V, I _F =13A, dI _F /dt=100A/μs
*Q _{rr}	-	81.9	-	nC	

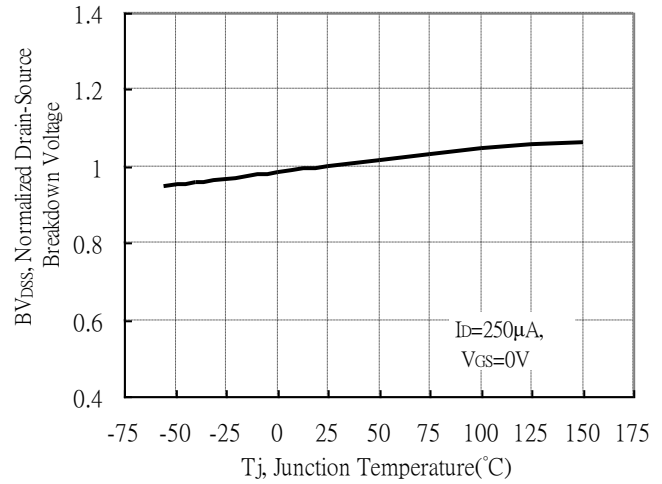
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

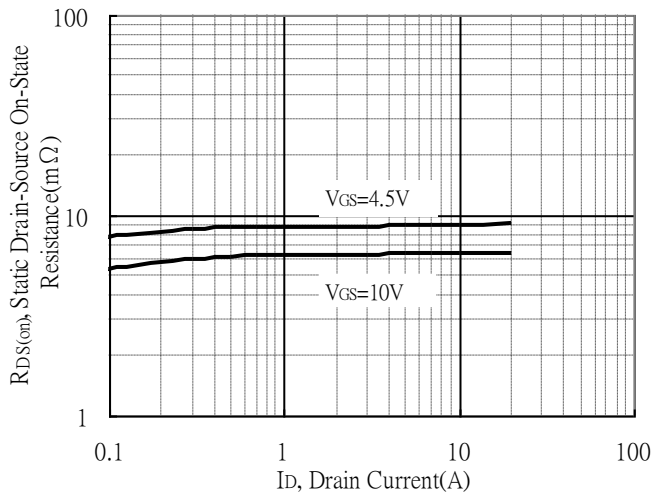
Typical Output Characteristics



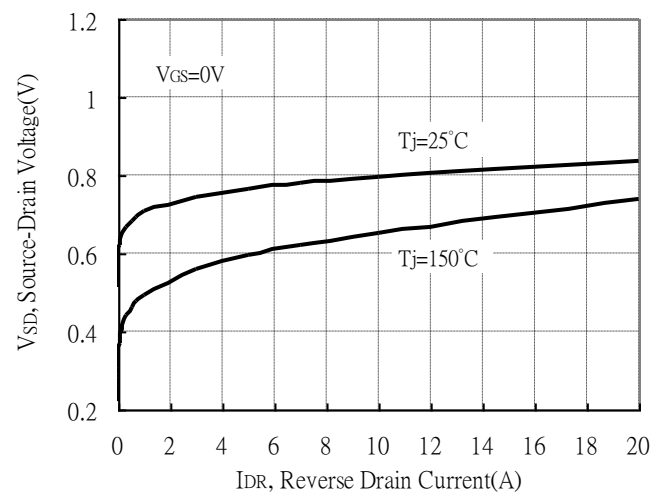
Brekdown Voltage vs Ambient Temperature



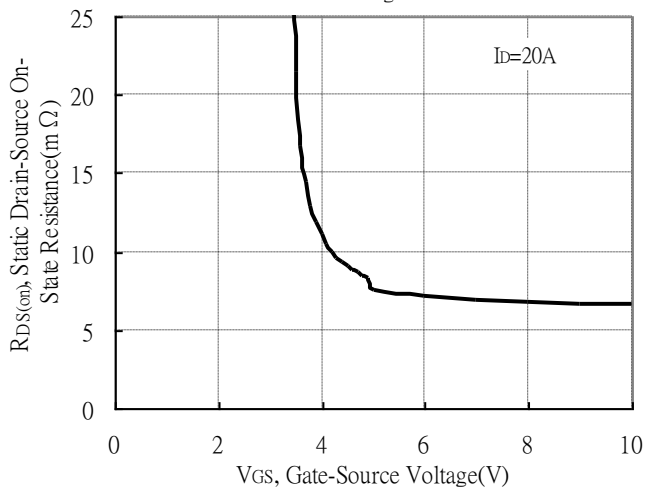
Static Drain-Source On-State resistance vs Drain Current



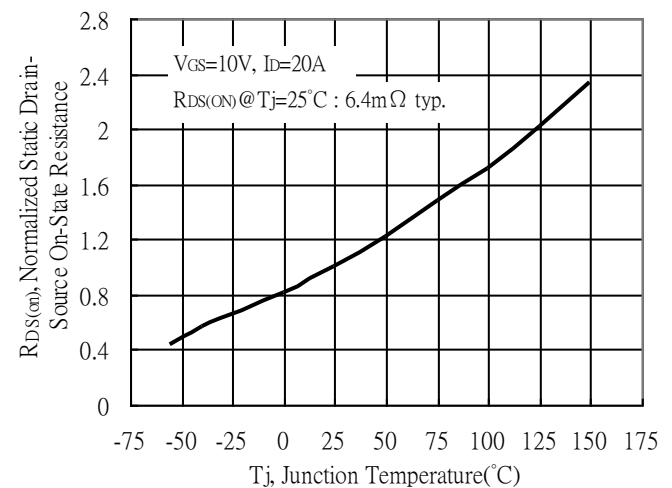
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

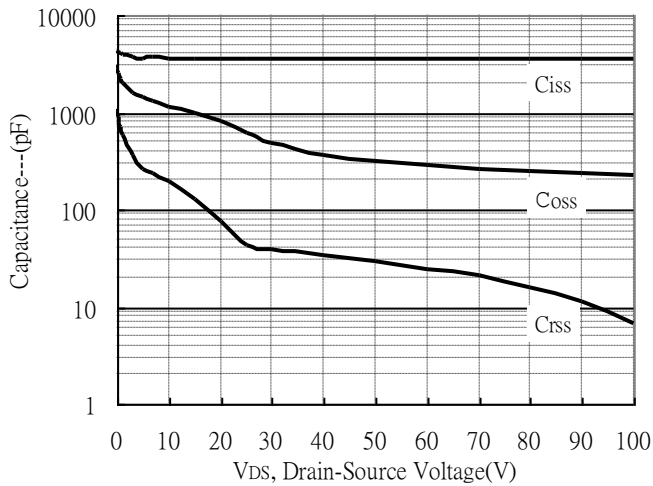


Drain-Source On-State Resistance vs Junction Temperature

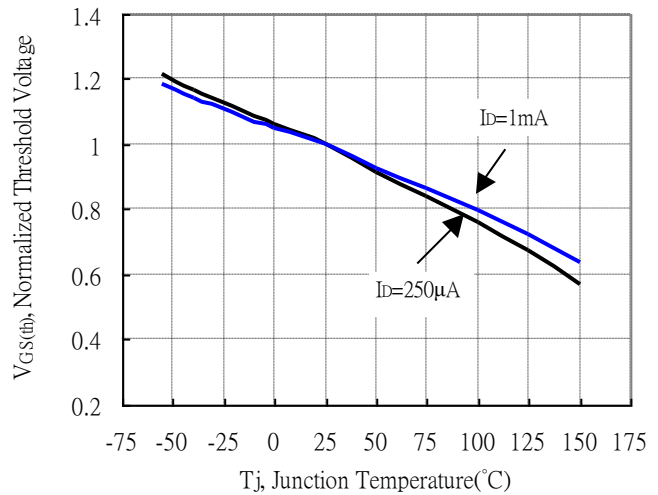


Typical Characteristics(Cont.)

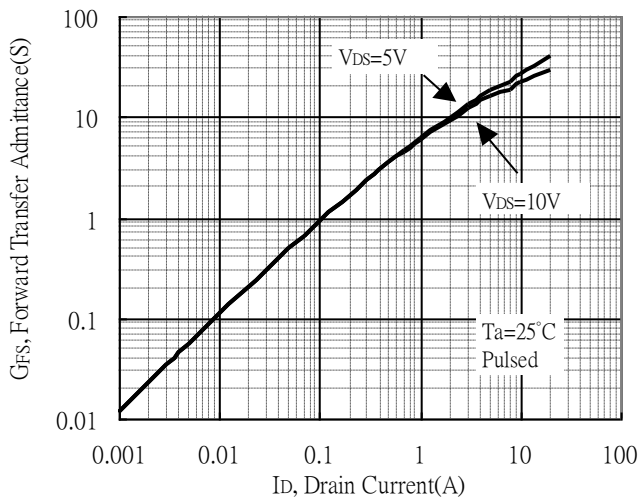
Capacitance vs Drain-to-Source Voltage



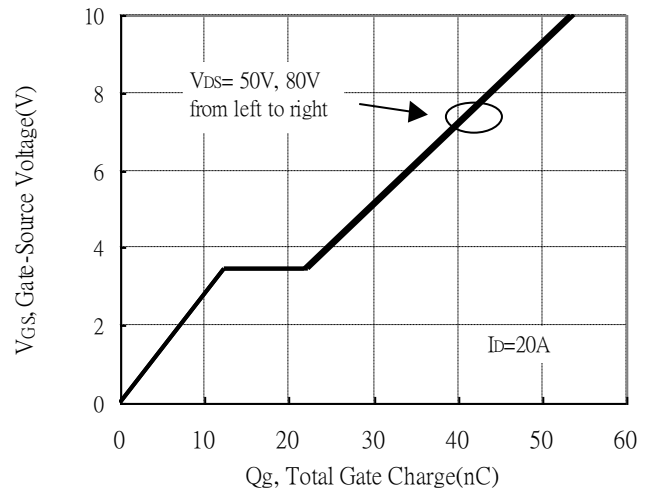
Threshold Voltage vs Junction Temperature



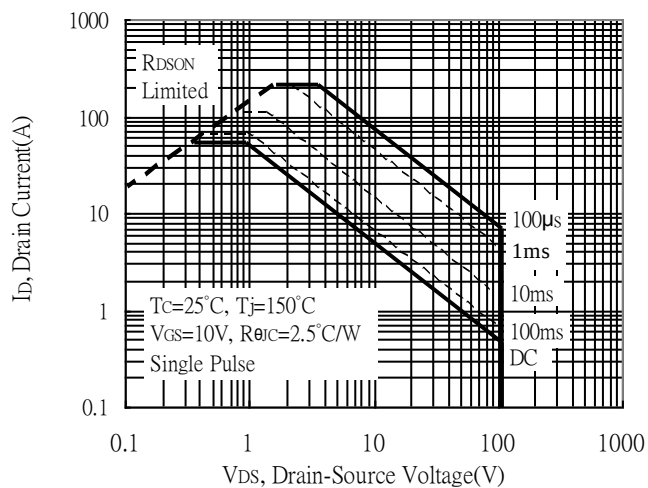
Forward Transfer Admittance vs Drain Current



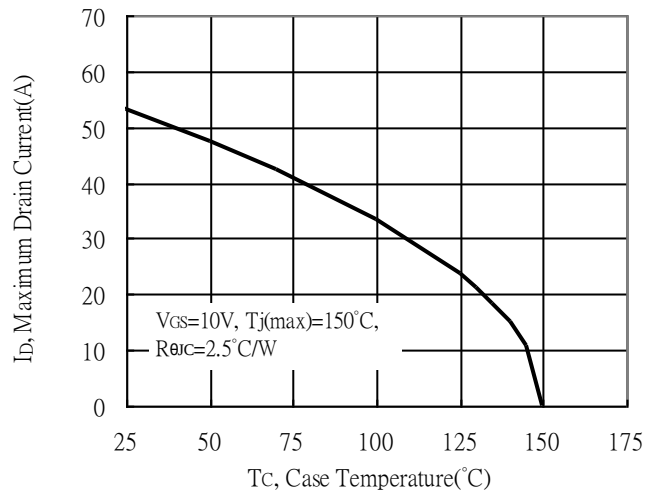
Gate Charge Characteristics



Maximum Safe Operating Area

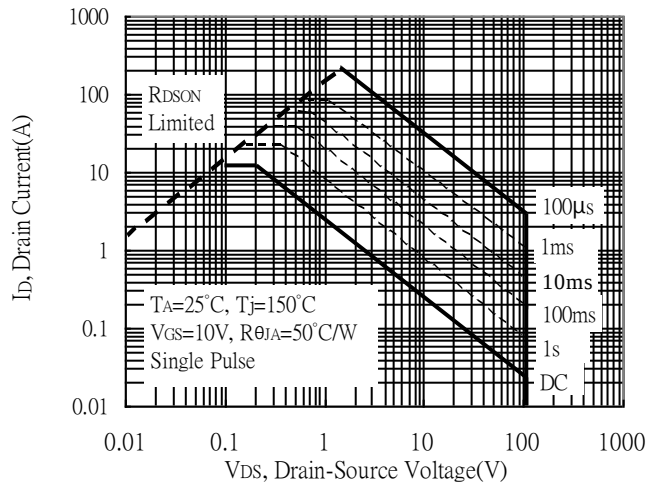


Maximum Drain Current vs Case Temperature

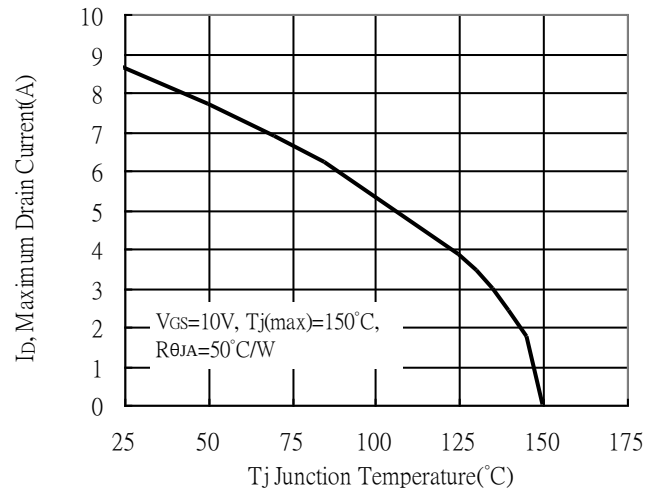


Typical Characteristics (Cont.)

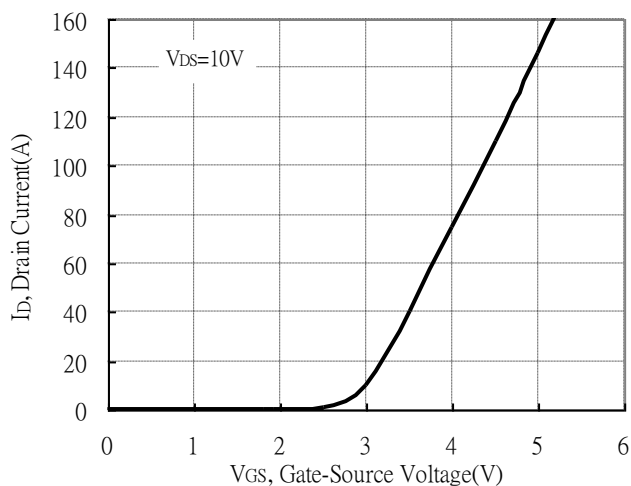
Maximum Safe Operating Area



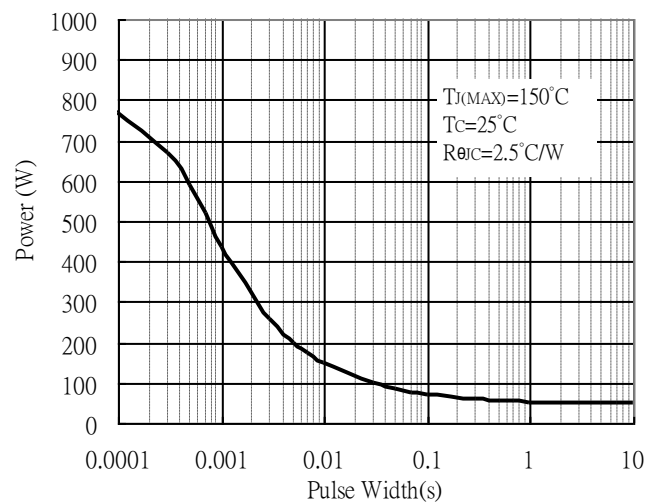
Maximum Drain Current vs Junction Temperature



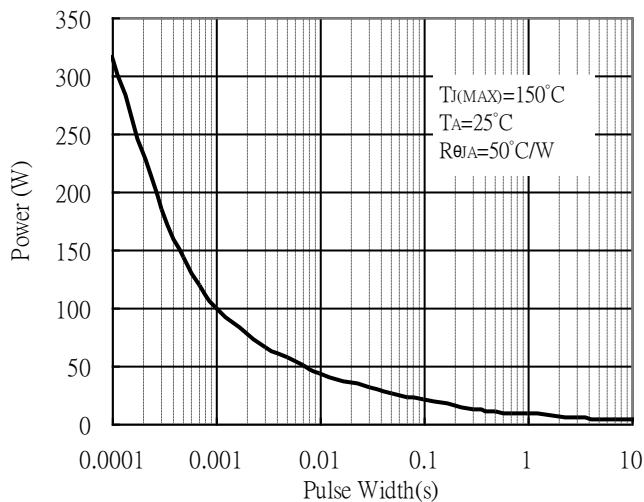
Typical Transfer Characteristics



Single Pulse Power Rating, Junction to Case

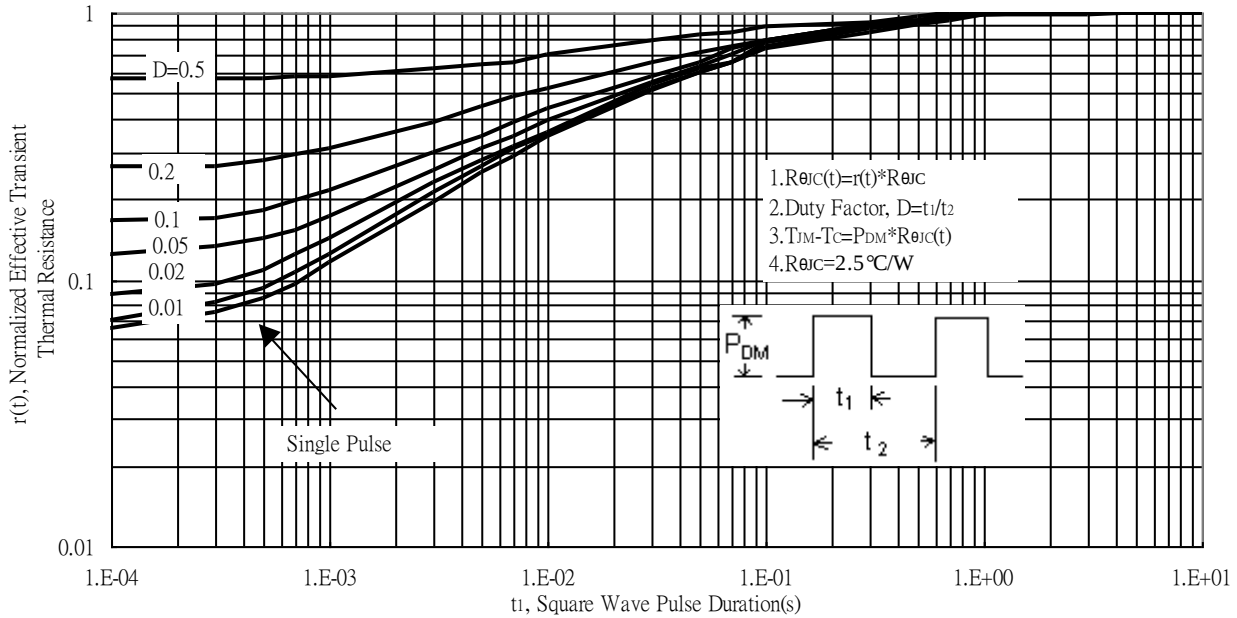


Single Pulse Power Rating, Junction to Case

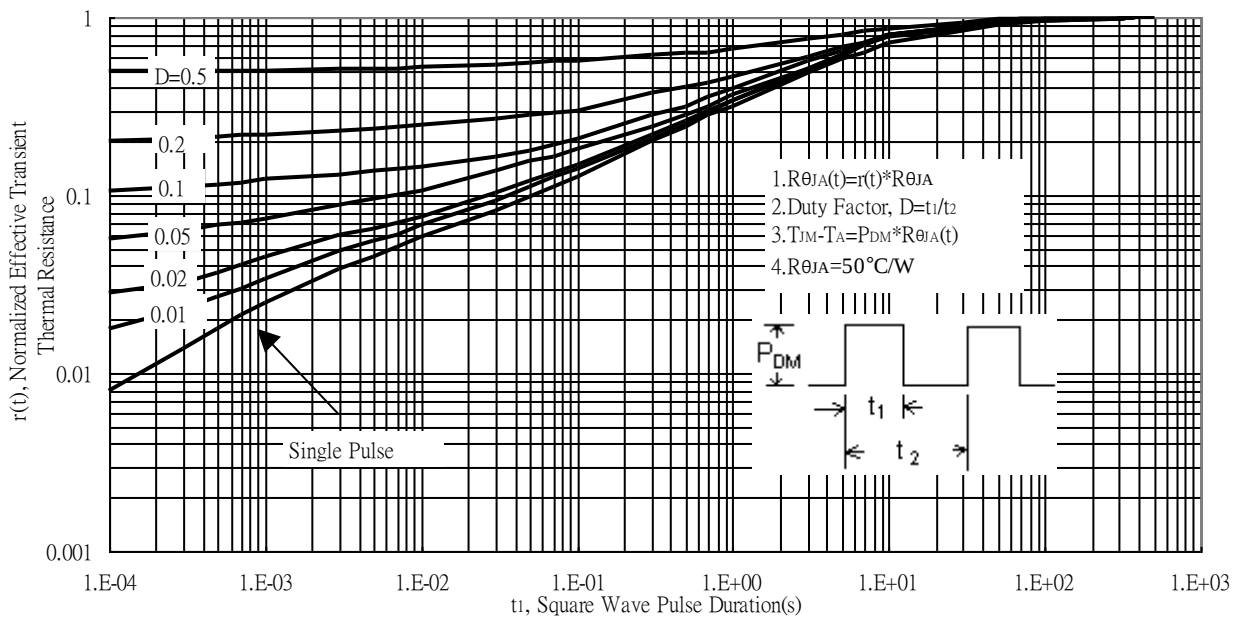


Typical Characteristics (Cont.)

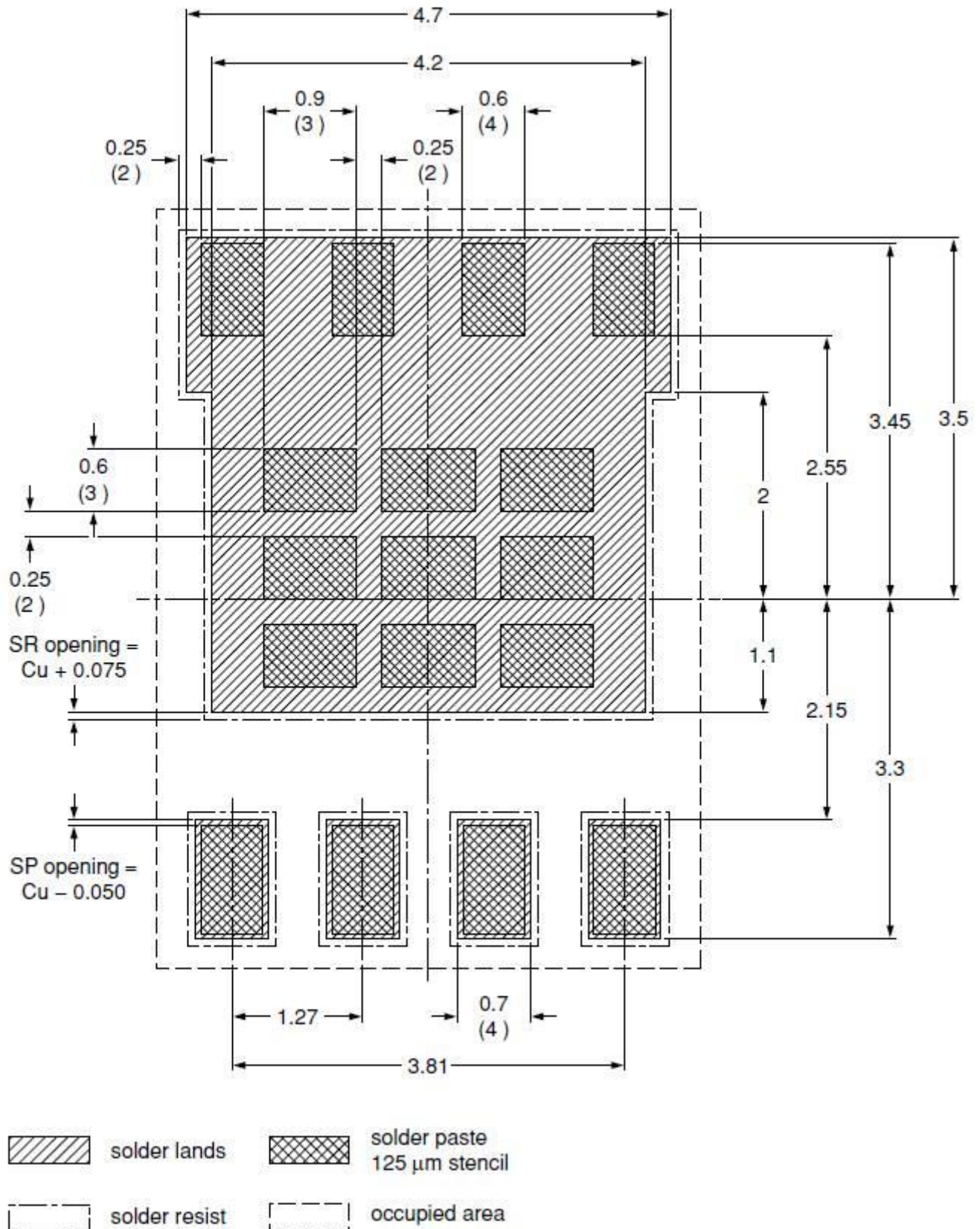
Transient Thermal Response Curves



Transient Thermal Response Curves

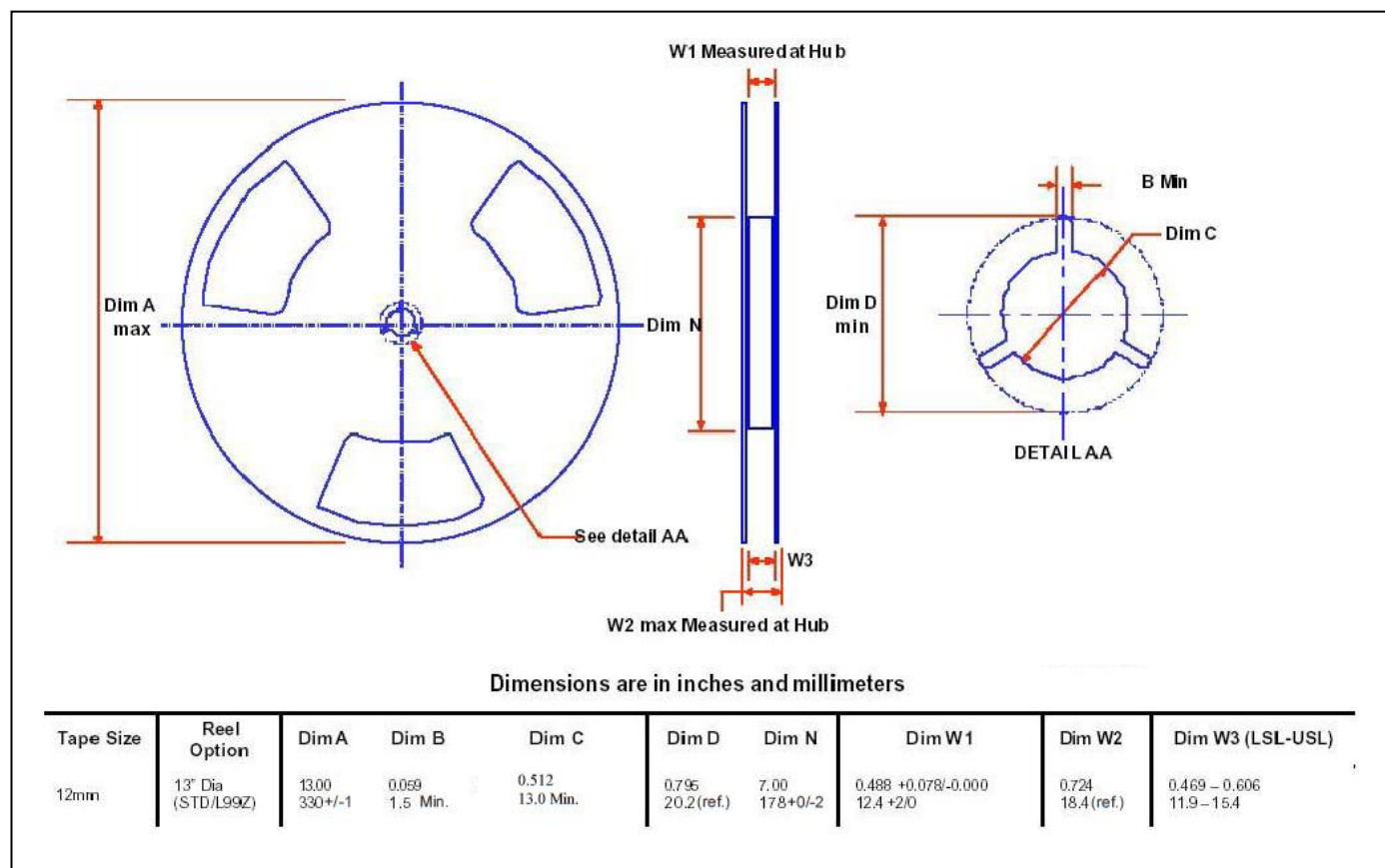


Recommended Soldering Footprint & Stencil Design

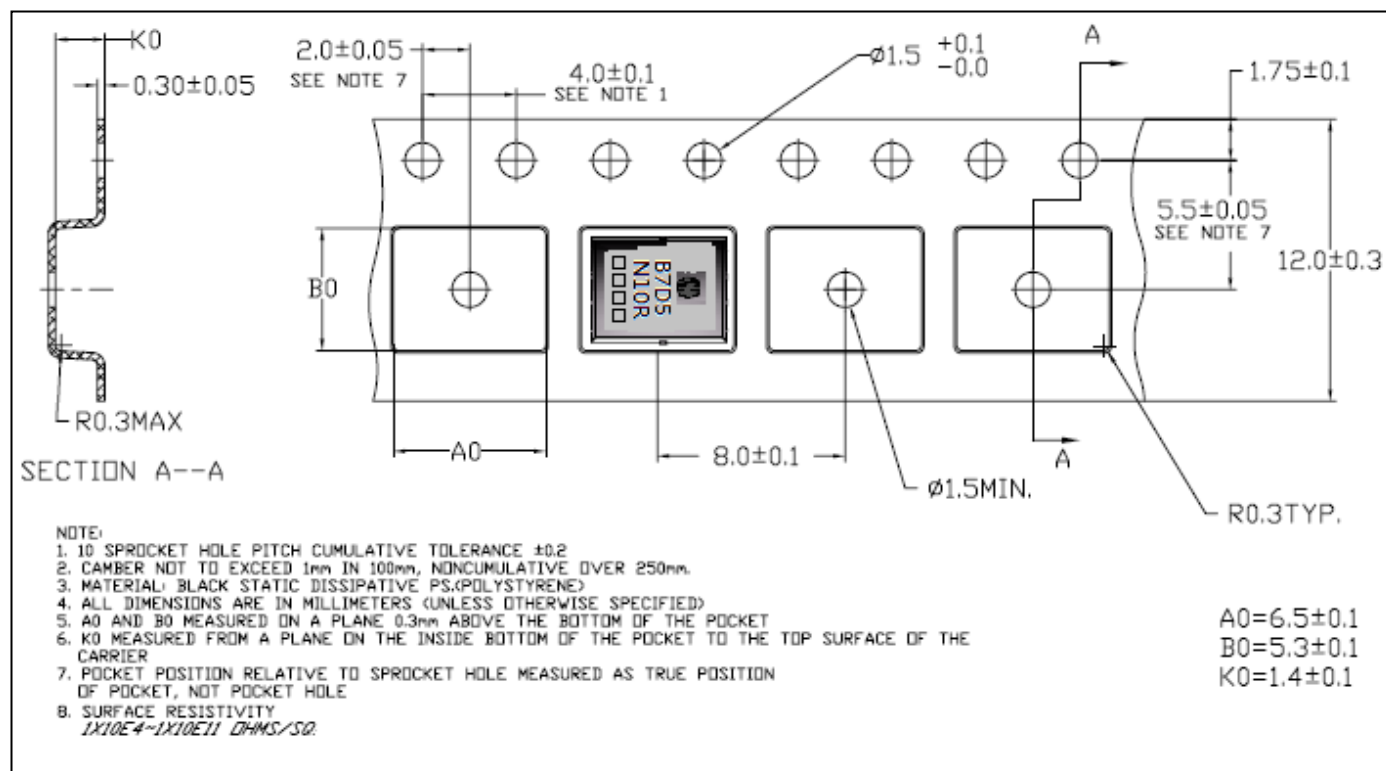


unit : mm

Reel Dimension



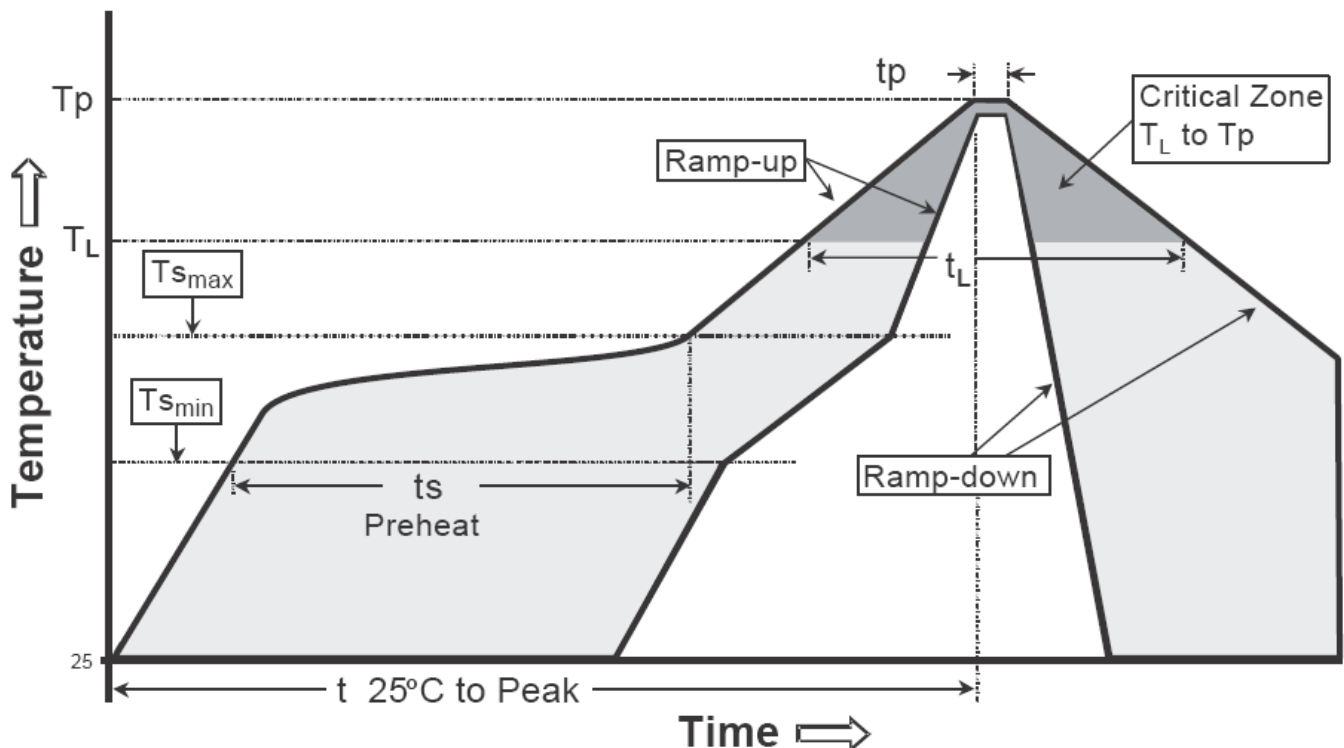
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

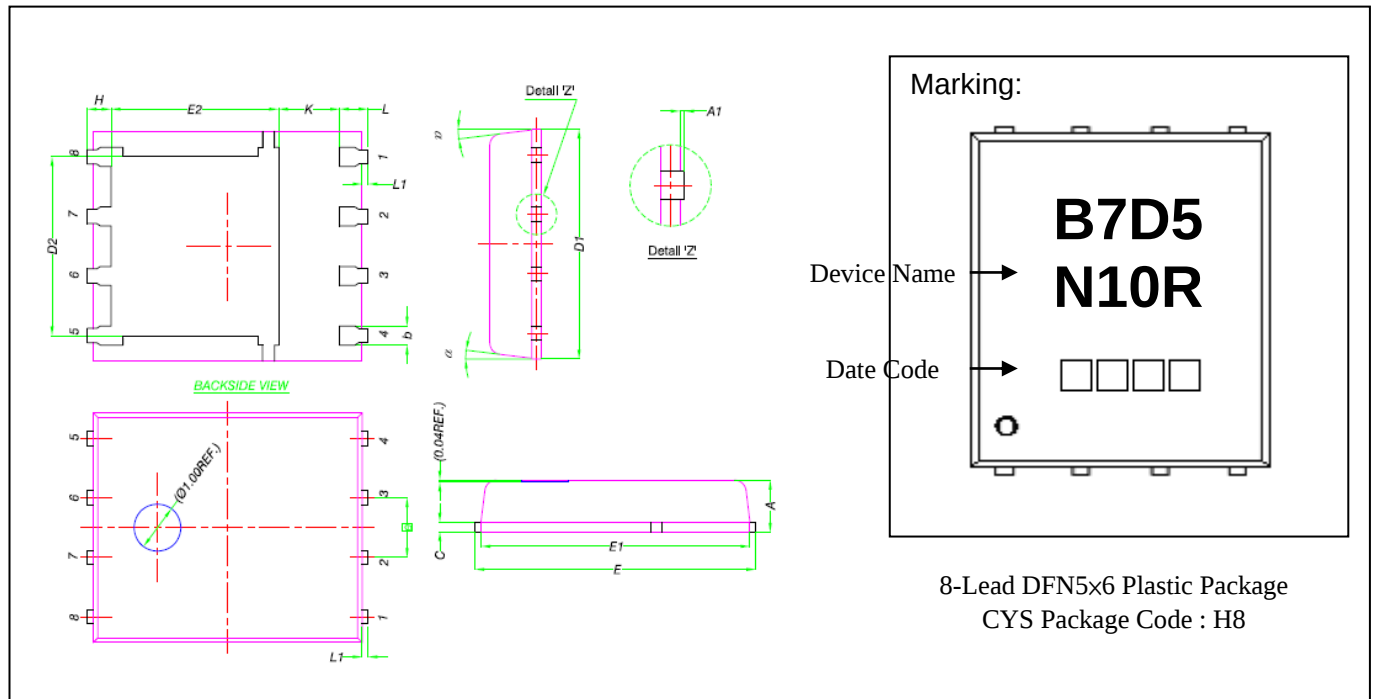
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T_{smax} to T_p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T_{smin})	100°C	150°C
-Temperature Max(T_{smax})	150°C	200°C
-Time(t_{smin} to t_{smax})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T_L)	183°C	217°C
- Time (t_L)	60-150 seconds	60-150 seconds
Peak Temperature(T_p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t_p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

DFN5x6 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.90	1.10	0.035	0.043	E2	3.38	3.78	0.133	0.149
A1	0.00	0.05	0.000	0.002	e	1.27	BSC	0.050	BSC
b	0.33	0.51	0.013	0.020	H	0.41	0.61	0.016	0.024
C	0.20	0.30	0.008	0.012	K	1.10	-	0.043	-
D1	4.80	5.00	0.189	0.197	L	0.51	0.71	0.020	0.028
D2	3.61	3.96	0.142	0.156	L1	0.06	0.20	0.002	0.008
E	5.90	6.10	0.232	0.240	θ	8°	12°	8°	12°
E1	5.70	5.80	0.224	0.228					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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